

Attorney Docket No. YOR920030585US1

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Patent Application

Applicant(s): Brian Allan Floyd
Docket No.: YOR920030585US1
Serial No.: 10/731,341
Filing Date: December 9, 2003
Group: 2817
Examiner: To Be Assigned

I hereby certify that this paper is being deposited on this date with the U.S. Postal Service as first class mail addressed to the Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

Signature: V. Benicewicz Date: March 15, 2004

Title: Millimeter-Wave Unilateral Low-Noise Amplifier

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Sir:

Pursuant to 37 C.F.R. §§1.56, 1.97 and 1.98, Applicant's attorney wishes to bring to the attention of the Patent and Trademark Office the following documents listed on the accompanying Form PTO-1449. A copy of each listed document is enclosed.

1. L. Tran et al., "High Performance, High Yield Millimeter-Wave MMIC LNAs Using InP HEMTs," IEEE IMS Digest, p. 9-12, June 1996.
2. M. Siddiqui et al., "GaAs Components for 60GHz Wireless Communication Applications," GaAs Mantech Conference, pp. 1-4, April 2002.
3. A. Fujihara et al., "High Performance 60-GHz Coplanar MMIC LNA Using InP Heterojunction FETs with AlAs/InAs Superlattice Layer," IEEE IMS Digest, p. 21-24, June 2000.
4. K. Nishikawa et al. "Compact LNA and VCO 3-D MMICs Using Commercial GaAs PHEMT Technology for V-band Single-chip TRX MMIC," IEEE IMS Digest, p. 1717-1720, June 2002.

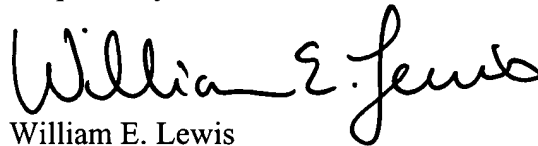
5. K. Onodera et al., "V-Band Monolithic Low-Noise Amplifiers Using Ion-Implanted n+-Self-Aligned GaAs MESFETs," IEEE Microwave Guided Wave Letters, Vol. 9, No. 4, pp. 148-150, April 1999.

6. B. Jagannathan et al., "Self-Aligned SiGe NPN Transistors with 285 GHz f_{MAX} and 207 GHz f_T in a Manufacturable Technology," IEEE Electron Device Letters, Vol. 23, No. 5, pp. 258-260, May 2002.

It is believed that there is no fee due in conjunction with the filing of this Information Disclosure Statement. In the event of non-payment or improper payment of a required fee, the Commissioner is authorized to charge or to credit **International Business Machines Corporation Deposit Account No. 50-0510** as required to correct the error.

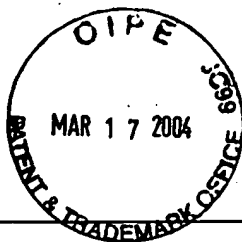
The filing of this Information Disclosure Statement shall not be construed as a representation that a search has been made, or as an admission that the information cited is considered to be material to patentability, or as a representation that no other material information exists.

Respectfully submitted,



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Date: March 15, 2004

FORM PTO-1449 (MODIFIED)**LIST OF PUBLICATIONS FOR
APPLICANT'S INFORMATION
DISCLOSURE STATEMENT**

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U.S. PATENT DOCUMENTS

| EXAMINER | | | | FILING DATE |
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| INITIAL | DOCUMENT NO. | DATE | NAME | IF APPROPRIATE |

FOREIGN PATENT DOCUMENTS

| EXAMINER | | | | TRANSLATION |
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| INITIAL | DOCUMENT NO. | DATE | COUNTRY | YES NO |

OTHER DOCUMENTS

| EXAMINER | | |
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| INITIAL | REF NO. | AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC. |

1. L. Tran et al., "High Performance, High Yield Millimeter-Wave MMIC LNAs Using InP HEMTs," IEEE IMS Digest, p. 9-12, June 1996.
2. M. Siddiqui et al., "GaAs Components for 60GHz Wireless Communication Applications," GaAs Mantech Conference, pp. 1-4, April 2002.
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Examiner

Date Considered

Examiner: Initial if reference considered, whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.